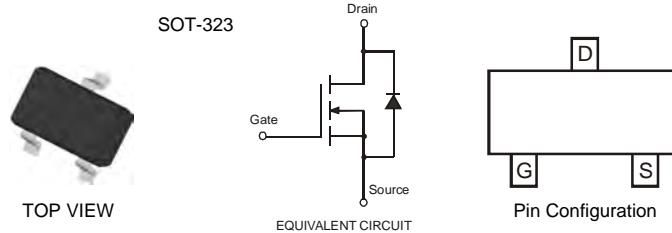


## Features

- Low On-Resistance:  
 $R_{DS(ON)} < 88m\Omega @ V_{GS} = 4.5V$   
 $R_{DS(ON)} < 138m\Omega @ V_{GS} = 2.5V$
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Lead Free By Design/RoHS Compliant (Note 2)**
- "Green" Device (Note 3)**
- Qualified to AEC-Q101 Standards for High Reliability**

## Mechanical Data

- Case: SOT-323
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020D
- Terminals: Finish - Matte Tin annealed over Alloy 42 leadframe. Solderable per MIL-STD-202, Method 208
- Terminal Connections: See Diagram
- Marking Information: See Page 3
- Ordering Information: See Page 3
- Weight: 0.006 grams (approximate)



## Maximum Ratings @ $T_A = 25^\circ C$ unless otherwise specified

Characteristic	Symbol	Value	Unit
Drain-Source Voltage	$V_{DSS}$	28	V
Gate-Source Voltage	$V_{GSS}$	$\pm 12$	V
Drain Current (Note 1)	$I_D$	1.6 1.2	A
		$T_A = 25^\circ C$ $T_A = 70^\circ C$	
Drain Current (Note 1)	$I_{DM}$	6.4	A
		Pulsed	
Body-Diode Continuous Current (Note 1)	$I_S$	1.5	A

## Thermal Characteristics

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 1)	$P_D$	350	mW
Thermal Resistance, Junction to Ambient @ $T_A = 25^\circ C$ (Note 1)	$R_{\theta JA}$	357	$^\circ C/W$
Operating and Storage Temperature Range	$T_J, T_{STG}$	-55 to +150	$^\circ C$

## Electrical Characteristics @ $T_A = 25^\circ C$ unless otherwise specified

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS (Note 4)</b>						
Drain-Source Breakdown Voltage	$BV_{DSS}$	28	—	—	V	$V_{GS} = 0V, I_D = 250\mu A$
Zero Gate Voltage Drain Current	$I_{DSS}$	—	—	800	nA	$V_{DS} = 28V, V_{GS} = 0V$
Gate-Body Leakage	$I_{GSS}$	—	—	$\pm 80$ $\pm 800$	nA	$V_{GS} = \pm 12V, V_{DS} = 0V$ $V_{GS} = \pm 19V, V_{DS} = 0V$
<b>ON CHARACTERISTICS (Note 4)</b>						
Gate Threshold Voltage	$V_{GS(th)}$	0.62	0.94	1.4	V	$V_{DS} = V_{GS}, I_D = 250\mu A$
Static Drain-Source On-Resistance	$R_{DS(ON)}$	—	73 115	88 138	$m\Omega$	$V_{GS} = 4.5V, I_D = 1.6A$ $V_{GS} = 2.5V, I_D = 1.2A$
Forward Transconductance	$ Y_{fs} $	—	5.4	—	S	$V_{DS} = 5V, I_D = 2.7A$
Source-Drain Diode Forward Voltage	$V_{SD}$	—	—	1.16	V	$V_{GS} = 0V, I_S = 1.5A$
<b>DYNAMIC CHARACTERISTICS</b>						
Input Capacitance	$C_{iss}$	—	305	—	pF	$V_{DS} = 5V, V_{GS} = 0V$ $f = 1.0MHz$
Output Capacitance	$C_{oss}$	—	74	—	pF	
Reverse Transfer Capacitance	$C_{rss}$	—	48	—	pF	

- Notes:
- Device mounted on  $1in^2$  FR-4 PCB on 2oz. Copper.  $t \leq 10$  sec.
  - No purposefully added lead.
  - Diodes Inc.'s "Green" policy can be found on our website at [http://www.diodes.com/products/lead\\_free/index.php](http://www.diodes.com/products/lead_free/index.php).
  - Short duration pulse test used to minimize self-heating effect.

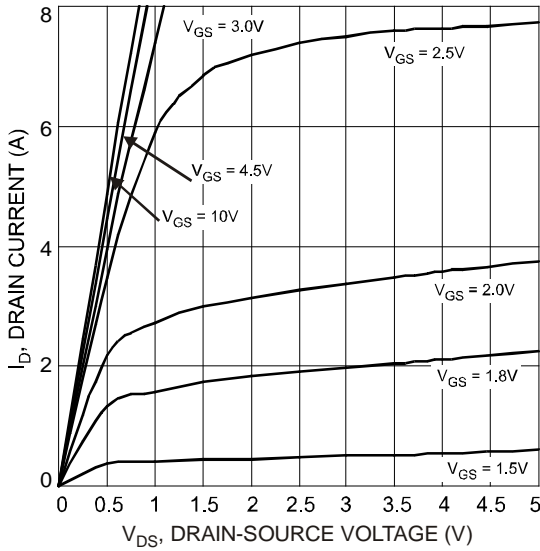


Fig. 1 Typical Output Characteristics

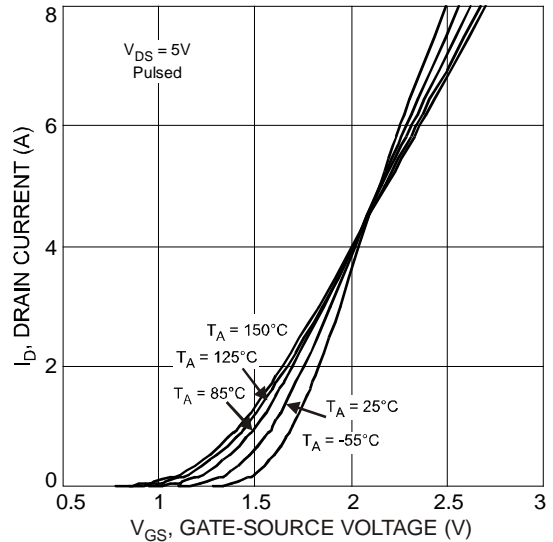


Fig. 2 Typical Transfer Characteristics

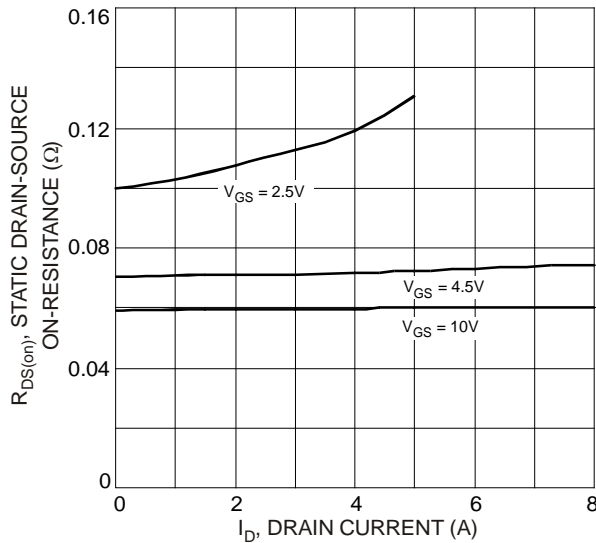


Fig. 3 On-Resistance vs. Drain Current and Gate Voltage

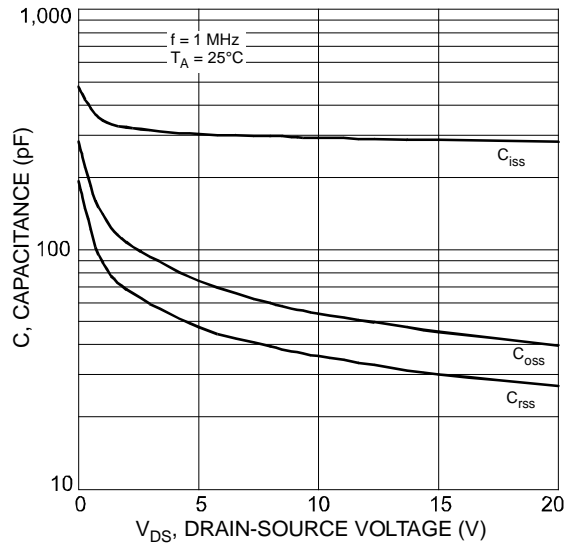


Fig. 4 Typical Total Capacitance

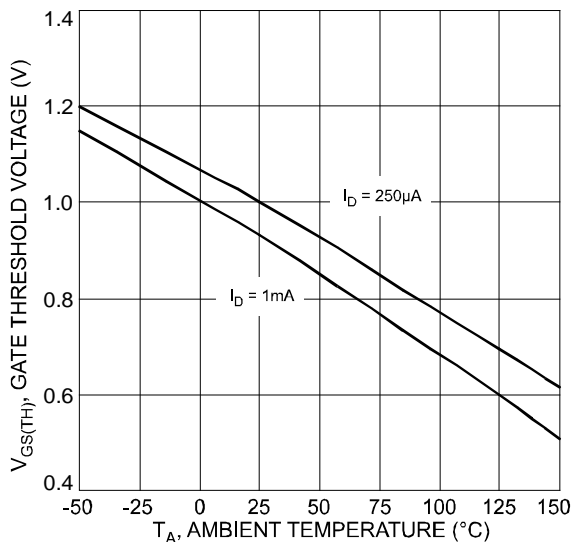


Fig. 5 Gate Threshold Voltage vs. Ambient Temperature

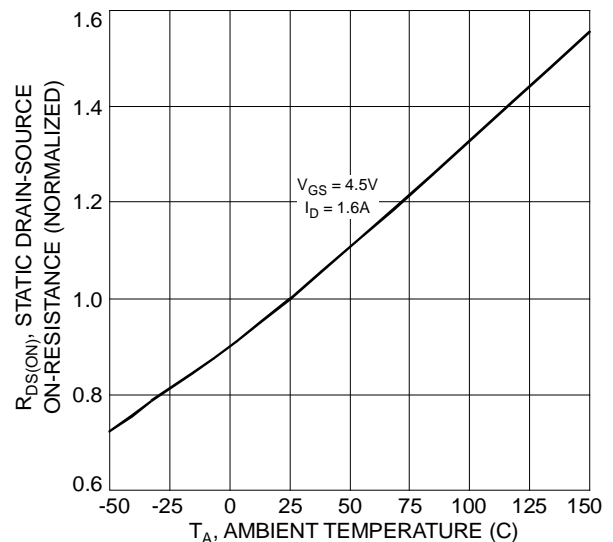


Fig. 6 Normalized Static Drain-Source On-Resistance vs. Ambient Temperature

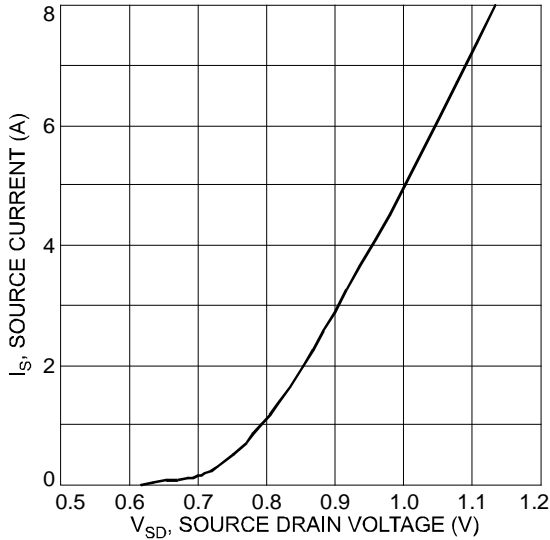


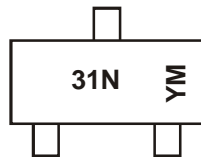
Fig. 7 Reverse Drain Current vs. Source-Drain Voltage

**Ordering Information** (Note 5)

Part Number	Case	Packaging
DMN3150LW-7	SOT-323	3000/Tape & Reel

Notes: 5. For packaging details, go to our website at <http://www.diodes.com/datasheets/ap02007.pdf>.

**Marking Information**



31N = Product Type Marking Code  
 YM = Date Code Marking  
 Y = Year (ex: V = 2008)  
 M = Month (ex: 9 = September)

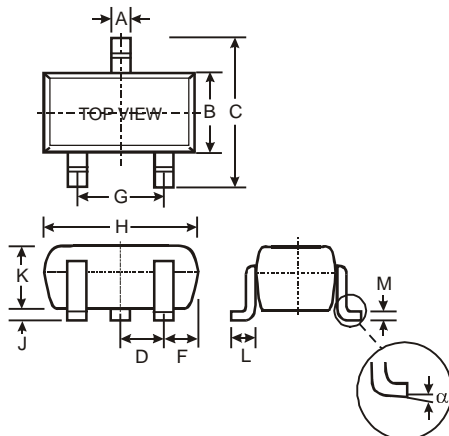
Date Code Key

Year	2008	2009	2010	2011	2012	2013	2014	2015
Code	V	W	X	Y	Z	A	B	C

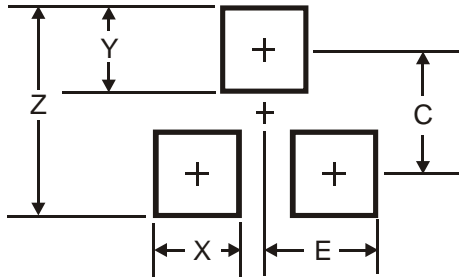
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

**Package Outline Dimensions**



SOT-323			
Dim	Min	Max	Typ
A	0.25	0.40	0.30
B	1.15	1.35	1.30
C	2.00	2.20	2.10
D	-	-	0.65
F	0.30	0.40	0.425
G	1.20	1.40	1.30
H	1.80	2.20	2.15
J	0.0	0.10	0.05
K	0.90	1.00	1.00
L	0.25	0.40	0.30
M	0.10	0.18	0.11
α	0°	8°	-
All Dimensions in mm			

**Suggested Pad Layout**



Dimensions	Value (in mm)
Z	2.8
X	0.7
Y	0.9
C	1.9
E	1.0

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